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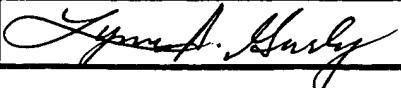
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Complete if Known	
Application Number	10/788,991
Filing Date	February 27, 2004
First Named Inventor	Paul A. Farrar
Group Art Unit	2812
Examiner Name	L. Gurley
Attorney Docket Number	2269-5570 IUS (02-1122 01/LIS)

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		ANDRICACOS, Panos C., "Copper On-Chip Interconnections", The Electrochemical Society Interface, Spring 1999, pp. 32-37, Vol. 8, No. 1.	
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		LYMAN et al., "Metallography, Structures and Phase Diagrams", Metals Handbook, 8 th Edition, date unknown, pp. 300-302, Vol. 8, Metals Park, Ohio.	
		MARCADAL et al., "OMCVD Copper Process for Dual Damascene Metallization", VMIC Conference, June 1997, pp. 93-98, 1997 ISMIC - 107/97/0093(c).	
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		SAARIVIRTA, Matti J., "High Conductivity Copper-Rich Cu-Zr Alloys", Transactions of the Metallurgical Society of AIME, June 1960, pp. 431-437, Vol. 218, New York, NY.	

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